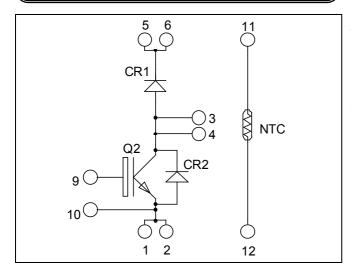
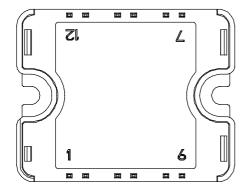


## Boost chopper Trench + Field Stop IGBT4 Power module





Pins 1/2; 3/4; 5/6 must be shorted together

# $V_{CES} = 1200V$ $I_C = 90A @ Tc = 80°C$

#### Application

- AC and DC motor control
- Switched Mode Power Supplies
- Power Factor Correction

#### **Features**

- Trench + Field Stop IGBT 4 Technology
  - Low voltage drop
  - Low leakage current
  - Low switching losses
  - Soft recovery parallel diodes
  - Low diode VF
  - Low leakage current
  - RBSOA and SCSOA rated
  - Symmetrical design
- Kelvin emitter for easy drive
- Very low stray inductance
- High level of integration
- Internal thermistor for temperature monitoring

#### **Benefits**

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- RoHS Compliant

### Absolute maximum ratings

Symbol	Parameter		Max ratings	Unit
$V_{CES}$	Collector - Emitter Breakdown Voltage		1200	V
Ţ	Continuous Collector Current	$T_c = 25^{\circ}C$	110	
$I_{\rm C}$	Continuous Conector Current	$T_c = 80$ °C	90	Α
$I_{CM}$	Pulsed Collector Current	$T_c = 25^{\circ}C$	150	
$V_{GE}$	Gate – Emitter Voltage		±20	V
$P_{D}$	Maximum Power Dissipation	$T_c = 25^{\circ}C$	385	W
RBSOA	Reverse Bias Safe Operating Area	$T_{j} = 150^{\circ}C$	150A @ 1150V	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com



### All ratings @ $T_j = 25$ °C unless otherwise specified

### **Electrical Characteristics**

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
$I_{CES}$	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 1200V$				250	μΑ
V <sub>CE(sat)</sub>	Collector Emitter saturation Voltage	$V_{GE} = 15V$	$T_j = 25$ °C		1.85	2.25	V
		$I_C = 75A \qquad T_j = 150^{\circ}C$		2.25		·	
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}$ , $I_C = 3mA$		5.0	5.8	6.5	V
$I_{GES}$	Gate – Emitter Leakage Current	$V_{GE} = 20V, V_{CE} = 0V$				600	nA

**Dynamic Characteristics** 

·	Characteristic	Test Conditions	5	Min	Typ	Max	Unit
Cies	Input Capacitance	$V_{GE} = 0V$	$V_{GE} = 0V$ $V_{CE} = 25V$		4.4		
$C_{oes}$	Output Capacitance				0.29		nF
$C_{res}$	Reverse Transfer Capacitance	f = 1MHz			0.24		
$Q_{G}$	Gate charge	$V_{GE} = \pm 15V$ ; $V_{GE} = 15V$	$V_{GE} = \pm 15V ; V_{CE} = 600V$ $I_{C} = 75A$		0.57		μС
$T_{d(on)}$	Turn-on Delay Time		Inductive Switching (25°C)		130		
$T_{\rm r}$	Rise Time	$V_{GE} = \pm 15V$			20		ns
$T_{d(off)}$	Turn-off Delay Time	$V_{\text{Bus}} = 600V$ $I_{\text{C}} = 75A$			300		
$T_{\mathrm{f}}$	Fall Time	$R_G = 2.2\Omega$			45		
$T_{d(on)}$	Turn-on Delay Time		Inductive Switching (150°C) $V_{GE} = \pm 15V$ $V_{Bus} = 600V$ $I_{C} = 75A$ $R_{G} = 2.2\Omega$		150		ns
T <sub>r</sub>	Rise Time	_			35		
$T_{d(off)}$	Turn-off Delay Time	***			350		
$T_{\rm f}$	Fall Time	$R_G = 2.2\Omega$			80		
Eon	Turn-on Switching Energy	$V_{GE} = \pm 15V$	$T_J = 25^{\circ}C$		3.4		mJ
Lon	Turn-on Switching Energy	$V_{Bus} = 600V$	$T_J = 150$ °C		8.5		1117
$E_{\text{off}}$	Turn-off Switching Energy	$I_C = 75A$	$T_J = 25^{\circ}C$		4.2		mJ
Loff	Turn-on Switching Elicity	$R_G = 2.2\Omega$	$T_{\rm J} = 150^{\circ}{\rm C}$		7.2		1113
$I_{sc}$	Short Circuit data	$V_{GE} \le 15V$ ; $V_{Bu}$ $t_p \le 10 \mu s$ ; $T_j = 1$			300		A

Chopper diode ratings and characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
$V_{RRM}$	Maximum Peak Repetitive Reverse Voltage			1200			V
$I_{RM}$	Maximum Reverse Leakage Current	$V_R = 1200V$	$T_j = 25^{\circ}C$			250	μΑ
$I_F$	DC Forward Current		$Tc = 80^{\circ}C$		90		A
$V_{\mathrm{F}}$	Diode Forward Voltage	$I_F = 75A$ $V_{GE} = 0V$	$T_i = 25^{\circ}C$		1.7	2.2	V
V F		$V_{GE} = 0V$	$T_{i} = 150^{\circ}C$		1.65		v
$t_{rr}$	Reverse Recovery Time	1 – 75 A	$T_j = 25$ °C		155		ns
· IT			$T_{j} = 150^{\circ}C$		300		115
0	Q <sub>rr</sub> Reverse Recovery Charge	$\begin{array}{l} I_F = 75A \\ V_R = 600V \\ di/dt = 1900A/\mu s \end{array}$	$T_j = 25$ °C		7.3		μС
Qrr			$T_{i} = 150^{\circ}C$		15.2		μС
Е	Ваханда Варахуану Енганду		$T_j = 25$ °C		2.6		mJ
$\mathbf{E}_{\mathrm{r}}$	E <sub>r</sub> Reverse Recovery Energy		$T_{\rm j} = 150^{\circ}{\rm C}$		5.5		1117



#### Thermal and package characteristics

Symbol	Characteristic			Min	Тур	Max	Unit
$R_{thJC}$	Junction to Case Thermal Resistance		IGBT			0.39	°C/W
KthJC			Diode			0.62	C/ VV
$V_{ISOL}$	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz			4000			V
$T_{J}$	Operating junction temperature range			-40		175	
$T_{STG}$	Storage Temperature Range		-40		125	°C	
$T_{\rm C}$	Operating Case Temperature			-40		100	
Torque	Mounting torque	To heatsink	M4	2		3	N.m
Wt	Package Weight					80	g

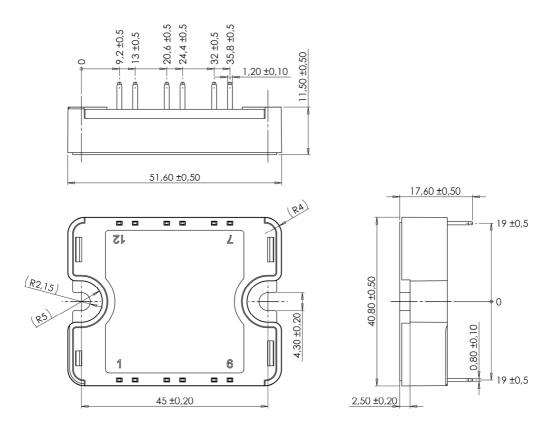
Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

Symbol	Characteristic		Min	Typ	Max	Unit
R <sub>25</sub>	Resistance @ 25°C			50		kΩ
$\Delta R_{25}/R_{25}$				5		%
$B_{25/85}$	$T_{25} = 298.15 \text{ K}$			3952		K
$\Delta \mathrm{B/B}$		T <sub>C</sub> =100°C		4		%

$$R_T = \frac{R_{25}}{\exp \left[ B_{25/85} \left( \frac{1}{T_{75}} - \frac{1}{T} \right) \right]} \quad \text{T: Thermistor temperature}$$

$$R_T: \text{ Thermistor value at T}$$

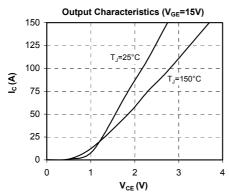
### SP1 Package outline (dimensions in mm)

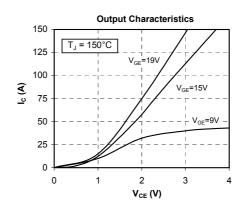


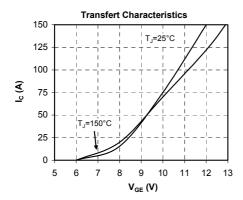
See application note 1904 - Mounting Instructions for SP1 Power Modules on www.microsemi.com

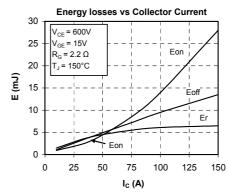


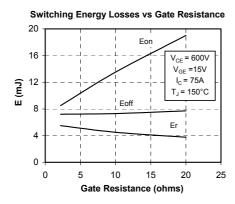
### **Typical Performance Curve**

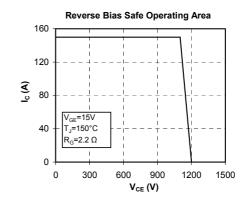


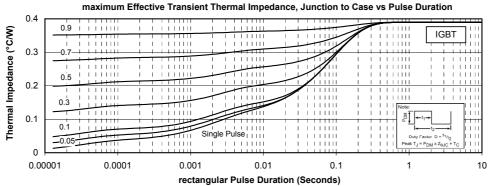




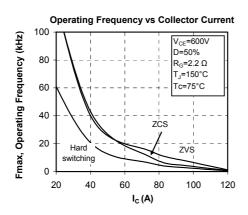


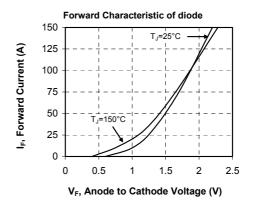


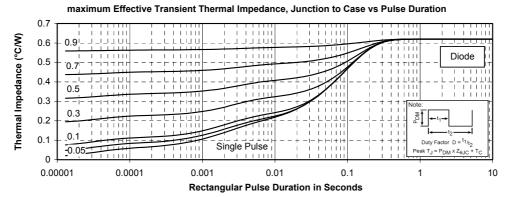












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